

## **PEM series**

#### 2.0 – 12.0 µm HgCdTe ambient temperature photoelectromagnetic detectors

**PEM series** features uncooled HgCdTe photovoltaic IR detectors based on photelectromagnetic effect in the semiconductor – spatial separation of optically generated electrons and holes in the magnetic field. The devices are designed for the maximum performance at 10.6 µm and especially useful as a large active area detectors to detect CW and low frequency modulated radiation. These devices are mounted in specialized packages with incorporated magnetic circuit inside. 3° wedged zinc selenide anti-reflection coated (wZnSeAR) window prevents unwanted interference effects and protects against pollution.

#### Spectral response (T<sub>a</sub> = 20°C)





PEM-TO8

PEM-SMA

#### Specification (T<sub>a</sub> = 20°C)

Parameter	Detector type	
	PEM-10.6	
Active element material	epitaxial HgCdTe heterostructure	
Optimum wavelength $\lambda_{opt}$ , $\mu m$	10.6	
Detectivity D*( $\lambda_{peak}$ ), cm·Hz <sup>1/2</sup> /W	≥2.0×10 <sup>7</sup>	
Detectivity D*( $\lambda_{opt}$ ), cm·Hz <sup>1/2</sup> /W	≥1.0×10 <sup>7</sup>	
Current responsivity-active area length product	>0.002	
R <sub>i</sub> (λ <sub>opt</sub> )·L, A·mm/W	_0.001	
Time constant τ, ns	≤1.2	
Resistance R, Ω	≥40	
Active area A, mm×mm	1×1, 2×2	
Package	PEM-SMA	PEM-TO8
Acceptance angle $\Phi$	~48°	~52°
Window	wZnSeAR	

#### Mechanical layout, mm



PEM-TO8



 $\Phi$  – acceptance angle

#### $\Phi$ – acceptance angle







# Spectral transmission of wZnSeAR window (typical example)



### **Dedicated preamplifier**



standard MIP